

GaAs Infrared Emitter

OPE5594A

The **OPE5594S** is GaAlAs infrared emitting diode that is designed for high reliability, high radiant intensity and low forward voltage. This device is optimized for efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T1-3/4 plastic package and has narrow beam angle with lensed package and cup frame.

FEATURES

- High-output power
- Narrow beam angle
- High reliability and long term stability
- Available for pulse operating

APPLICATIONS

- Optical emitters
- Optical switches
- Smoke sensors
- IR remote control
- IR sound transmission

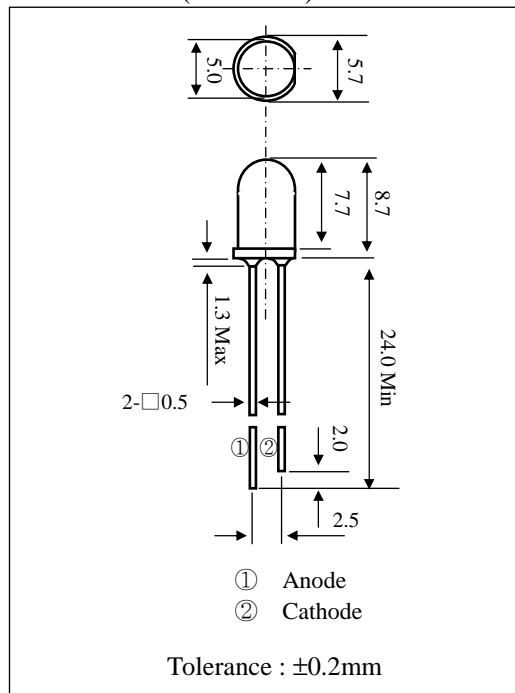
STORAGE

- Condition : 5°C~35°C,R.H.60%
- Terms : within 3 months from production date
- Remark : Once the package is opened, the products should be used within a day.

Otherwise, it should be keeping in a damp proof box with desiccants.

* Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

DIMENSIONS (Unit : mm)



MAXIMUM RATINGS

(Ta=25°C)

Item	Symbol	Rating	Unit
Power Dissipation	P_D	150	mW
Forward current	I_F	100	mA
Pulse forward current	I_{FP}	1.0	A
Reverse voltage	V_R	5.0	V
Operating temp.	$T_{opr.}$	-25~+85	°C
Soldering temp.	$T_{sol.}$	260.	°C

*1. Duty ratio = 1/100, pulse width=0.1ms.

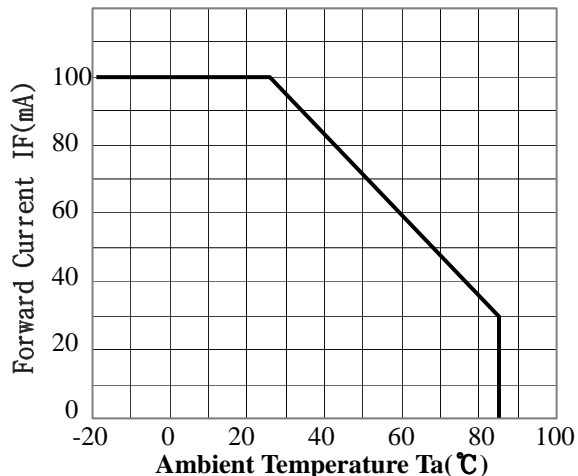
*2. Lead Soldering Temperature (2mm from case for 5sec.).

ELECTRO-OPTICAL CHARACTERISTICS

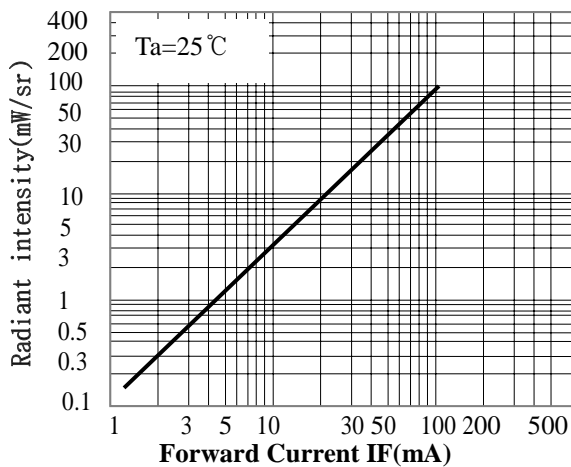
(Ta=25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward voltage	V_F	$I_F=100mA$		1.4	1.7	V
Reverse current	I_R	$V_R=5V$			10	μA
Capacitance	C_t	$f=1MHz$		20		pF
Radiant intensity	I_e	$I_F=100mA$		80		mW/sr
Peak emission wavelength	λ_p	$I_F=50mA$		940		nm
Spectral bandwidth 50%	$\Delta \lambda$	$I_F=50mA$		45		nm
Half angle	$\Delta \theta$	$I_F=100mA$		±10		deg.

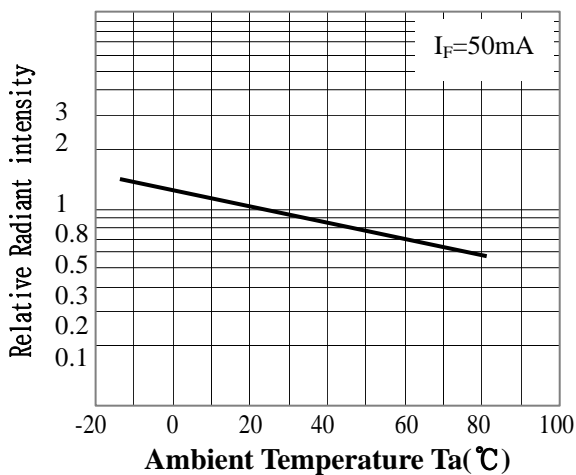
- FORWARD CURRENT Vs. AMBIENT TEMP.



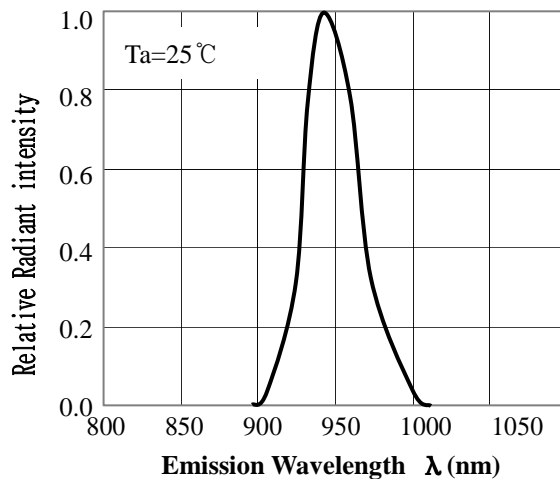
- RADIANT INTENSITY Vs. FORWARD CURRENT.



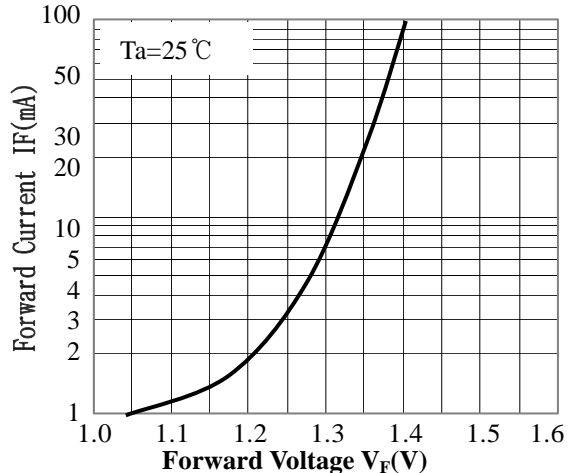
- RELATIVE RADIANT INTENSITY Vs. AMBIENT TEMP.



- RELATIVE RADIANT INTENSITY Vs. EMISSION WAVELENGTH.



- FORWARD CURRENT Vs. FORWARD VOLTAGE



- ANGULAR DISPLACEMENT Vs RELATIVE RADIANT INTENSITY

